

at least an n-type semiconductor layer, an active layer and a p-type semiconductor layer deposited in this order, and a p-side electrode and an n-side electrode, wherein the p-side electrode of the first laser unit is electrically connected to the n-side electrode of the second laser unit and the n-side electrode of the first laser unit is electrically connected to the p-side electrode of the second laser unit.

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2. (Amended) The semiconductor laser device according to claim 1, further comprising:
a first connecting layer interconnecting said p-side electrode of the first laser unit and said n-side electrode of the second laser unit; and
a second connecting layer interconnecting between said p-side electrode of the second laser unit and said n-side electrode of the first laser unit.

4. (Twice Amended) The semiconductor laser device according to claim 2, wherein at least one of said first and said second connecting layers has a Schottky barrier.
5. (Twice Amended) The semiconductor laser device according to claim 1, wherein at least one of the first and second laser units has a Schottky barrier between the p-side electrode and the p-type semiconductor layer.
6. (Twice Amended) The semiconductor laser device according to claim 1, wherein at least one of the first and second laser units is a semiconductor laser having a gallium nitride (GaN) system semiconductor deposited.

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10 ~~14~~ (Amended) The semiconductor laser device according to claim 2, wherein at least one of the first and second laser units is a semiconductor laser having a gallium nitride (GaN) system semiconductor deposited.

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11 ~~15~~ (Amended) The semiconductor laser device according to claim 3, wherein at least one of the first and second laser units is a semiconductor laser having a gallium nitride (GaN) system semiconductor deposited.

12 ~~16~~ (Amended) The semiconductor laser device according to claim 4, wherein at least one of the first and second laser units is a semiconductor laser having a gallium (GaN) system semiconductor deposited.

13 ~~18~~ (Amended) The semiconductor laser device according to claim 5, wherein at least one of the first and second laser units is a semiconductor laser having a gallium nitride (GaN) system semiconductor deposited.